

Listing of Claims:

Claims 1-17 (Cancelled)

Claim 18 (Currently Amended) An in-plane switching mode liquid crystal display (LCD) device comprising:

- a gate electrode on a substrate;
- a gate insulating film on an entire surface of the substrate;
- a semiconductor layer and an ohmic contact layer on the gate insulating film;
- a buffer layer on the ohmic contact layer;
- a pixel electrode on the buffer layer;
- source ~~and~~^{or} drain electrodes connected with the pixel electrodes on the buffer layer;
- a passivation layer on the pixel electrode; and
- a common electrode on the passivation layer.

Claim 19 (Original) The in-plane switching mode LCD device as claimed in claim 18, wherein the gate electrode includes a low resistance material.

Claim 20 (Original) The in-plane switching mode LCD device as claimed in claim 19, wherein the low resistance material includes one of aluminum (Al), copper (Cu), and silver (Ag).

Claim 21 (Original) The in-plane switching mode LCD device as claimed in claim 18, wherein the buffer layer includes a metal.

Claim 22 (Original) The in-plane switching mode LCD device as claimed in claim 21, wherein the buffer layer includes titanium (Ti).

Claim 23 (Original) The in-plane switching mode LCD device as claimed in claim 18, wherein the source and drain electrodes include a low resistance material.

Claim 24 (Original) The in-plane switching mode LCD device as claimed in claim 23, wherein the low resistance material includes one of aluminum (Al), copper (Cu), and silver (Ag).

Claim 25 (Original) The in-plane switching mode LCD device as claimed in claim 18, wherein the pixel electrode includes transparent conductive material.

Claim 26 (Original) The in-plane switching mode LCD device as claimed in claim 25, wherein the pixel electrode includes indium tin oxide.

Claim 27 (Original) The in-plane switching mode LCD device as claimed in claim 18, wherein the common electrode includes indium tin oxide.

Claim 28 (Original) A method for manufacturing an in-plane switching mode liquid crystal display (LCD) device comprising:

3, forming a gate electrode on a substrate;
forming a gate insulating film, a semiconductor layer, an ohmic contact layer, and a buffer layer on the gate electrode;
forming a pixel electrode on the buffer layer;
forming source and drain electrodes on the buffer layer;
forming a passivation layer on a surface of the substrate; and
forming a common electrode on the passivation layer.

Claim 29 (Original) The in-plane switching mode LCD device as claimed in claim 28, wherein the gate electrode includes one of aluminum (Al), copper (Cu), and silver (Ag).

Claim 30 (Original) The in-plane switching mode LCD device as claimed in claim 28, wherein the buffer layer includes titanium (Ti).

Claim 31 (Original) The in-plane switching mode LCD device as claimed in claim 28, wherein the source and drain electrodes include one of aluminum (Al), copper (Cu), and silver (Ag).

Claim 32 (Original) The in-plane switching mode LCD device as claimed in claim 28, wherein the pixel electrode includes indium tin oxide.

Claim 33 (Original) The in-plane switching mode LCD device as claimed in claim 28, wherein the drain electrode is electrically connected with the pixel electrode.

Claim 34 (Original) The in-plane switching mode LCD device as claimed in claim 28, wherein the common electrode includes indium tin oxide.

Claim 35 (Original) The in-plane switching mode LCD device as claimed in claim 28, wherein the gate electrode is deposited by a sputtering process.

8, Claim 36 (Original) The in-plane switching mode LCD device as claimed in claim 35, wherein the gate electrode is patterned using photolithography.

Claim 37 (Original) The in-plane switching mode LCD device as claimed in claim 28, wherein the semiconductor layer, the ohmic contact layer, and the buffer layer are formed on the gate insulating film by a plasma enhanced chemical vapor deposition (PECVD) process.

Claim 38 (Original) The in-plane switching mode LCD device as claimed in claim 37, wherein the semiconductor layer, the ohmic contact layer, and the buffer layer are patterned.

Claim 39 (Original) The in-plane switching mode LCD device as claimed in claim 28, wherein the pixel electrode is formed by a sputtering process.

Claim 40 (Original) The in-plane switching mode LCD device as claimed in claim 39, wherein the pixel electrode is patterned.

023
Claim 41 (Original) The in-plane switching mode LCD device as claimed in claim 28,
wherein the passivation layer is formed by a deposition process.
